ON Semiconductor®

FDMC7660

N-Channel PowerTrench® MOSFET
30 V, 20 A, 2.2 mΩ

Features

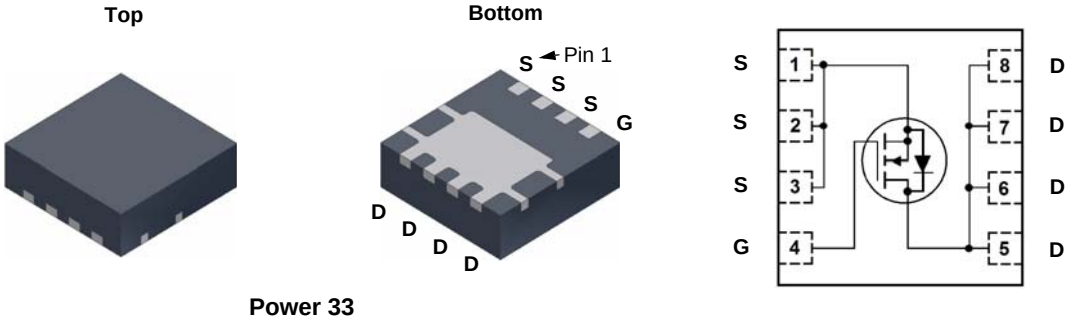
- Max $r_{DS(on)}$ = 2.2 mΩ at V_{GS} = 10 V, I_D = 20 A
- Max $r_{DS(on)}$ = 3.3 mΩ at V_{GS} = 4.5 V, I_D = 18 A
- High performance technology for extremely low $r_{DS(on)}$
- Termination is Lead-free and RoHS Compliant

General Description

This N-Channel MOSFET is produced using ON Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

Applications

- DC - DC Buck Converters
- Point of Load
- High Efficiency Load Switch and Low Side Switching



Power 33

MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			30	V
V_{GS}	Gate to Source Voltage		(Note 4)	±20	V
I_D	Drain Current -Continuous (Package limited)	T_C = 25°C		40	A
	-Continuous (Silicon limited)	T_C = 25°C		100	
	-Continuous	T_A = 25°C	(Note 1a)	20	
	-Pulsed			200	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	200	mJ
P_D	Power Dissipation	T_C = 25°C		41	W
	Power Dissipation	T_A = 25°C	(Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to + 150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC7660	FDMC7660	Power 33	13''	12 mm	3000 units

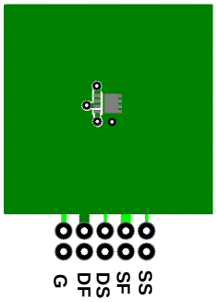
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Electrical Characteristics T_J = 25°C unless otherwise noted

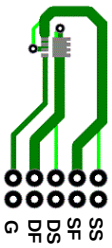
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C		14		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1.2	1.7	2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25°C		-6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 20 A		1.8	2.2	mΩ
		V_{GS} = 4.5 V, I_D = 18 A		2.6	3.3	
		V_{GS} = 10 V, I_D = 20 A, T_J = 125°C		2.2	3.1	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 20 A		163		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1MHz		3630	4830	pF
C_{oss}	Output Capacitance			1345	1790	pF
C_{rss}	Reverse Transfer Capacitance			110	165	pF
R_g	Gate Resistance			0.9		Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 15 V, I_D = 20 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		14	25	ns
t_r	Rise Time			6.8	14	ns
$t_{d(off)}$	Turn-Off Delay Time			36	58	ns
t_f	Fall Time			5.7	11	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V, V_{DD} = 15 V, I_D = 20 A		54	86	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V, V_{DD} = 15 V, I_D = 20 A		24	38	nC
Q_{gs}	Gate to Source Charge			11		nC
Q_{gd}	Gate to Drain “Miller” Charge			5.6		nC
Drain-Source Diode Characteristics						
V_{SD}	Source-Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 20 A (Note 2)		0.8	1.2	V
		V_{GS} = 0 V, I_S = 1.9 A (Note 2)		0.7	1.2	
t_{rr}	Reverse Recovery Time	I_F = 20 A, di/dt = 100 A/μs		45	63	ns
Q_{rr}	Reverse Recovery Charge			25	35	nC

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user’s board design.



a. 53 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 125 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. Starting T_J = 25 °C, L = 1 mH, I_{AS} = 20 A, V_{DD} = 27 V, V_{GS} = 10 V
4. As an N-channel device, the negative Vgs rating is for low duty cycle pulse ocurrence only. No continuous rating is implied.

Typical Characteristics T_J = 25°C unless otherwise noted

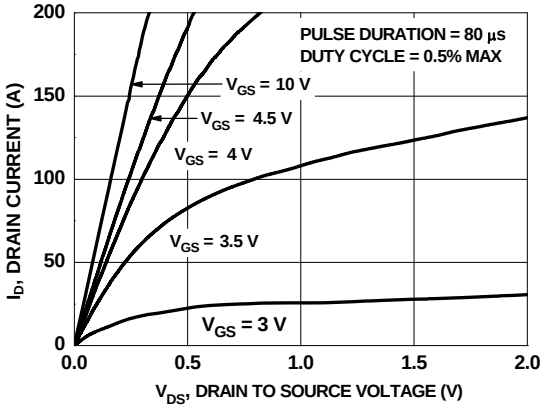


Figure 1. On Region Characteristics

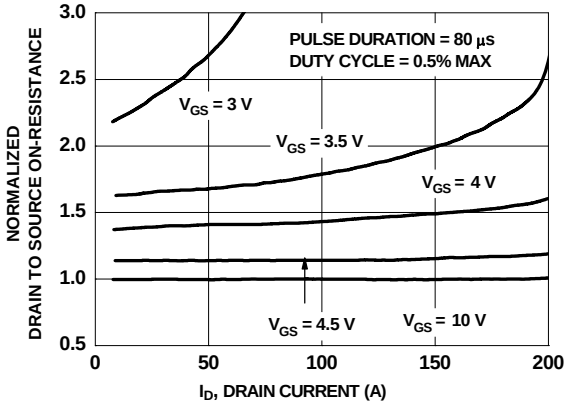


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

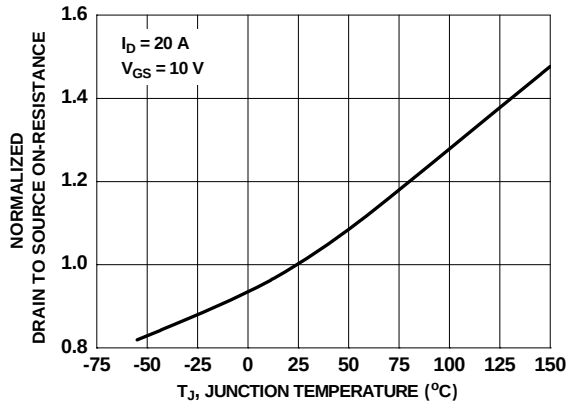


Figure 3. Normalized On Resistance vs Junction Temperature

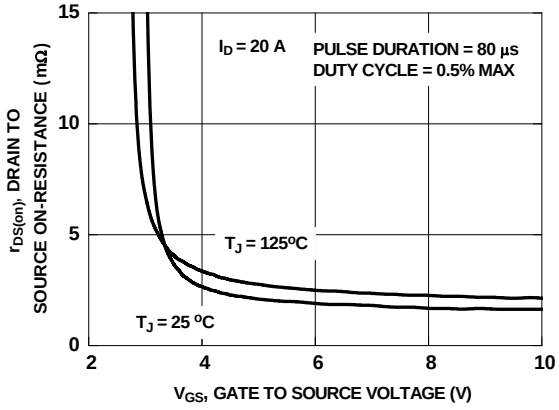


Figure 4. On-Resistance vs Gate to Source Voltage

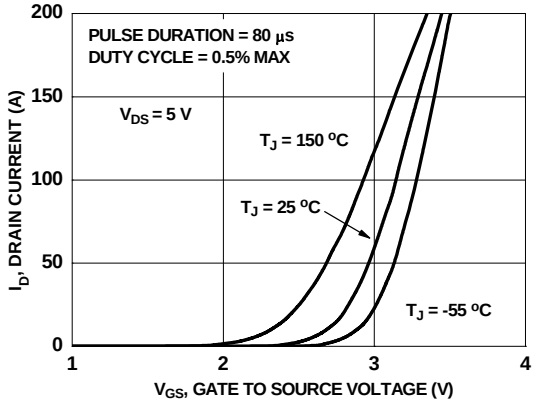


Figure 5. Transfer Characteristics

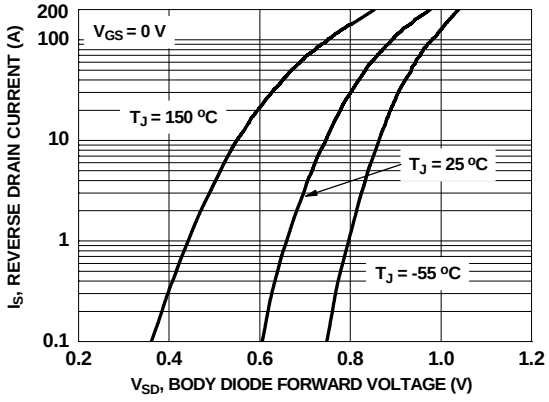


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25°C unless otherwise noted

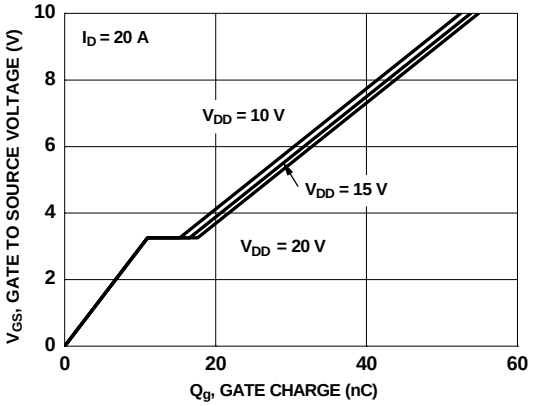


Figure 7. Gate Charge Characteristics

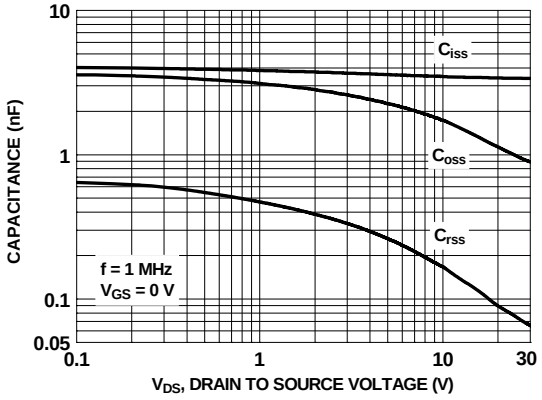


Figure 8. Capacitance vs Drain to Source Voltage

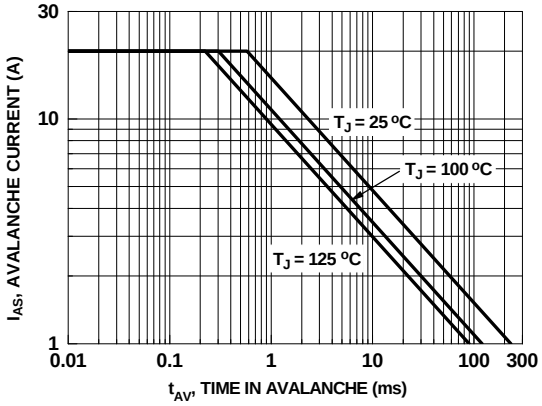


Figure 9. Unclamped Inductive Switching Capability

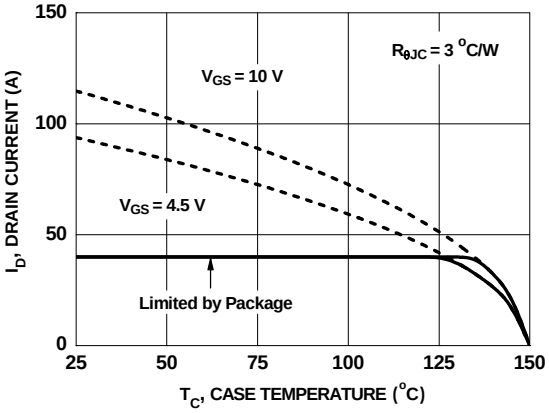


Figure 10. Maximum Continuous Drain Current vs Case Temperature

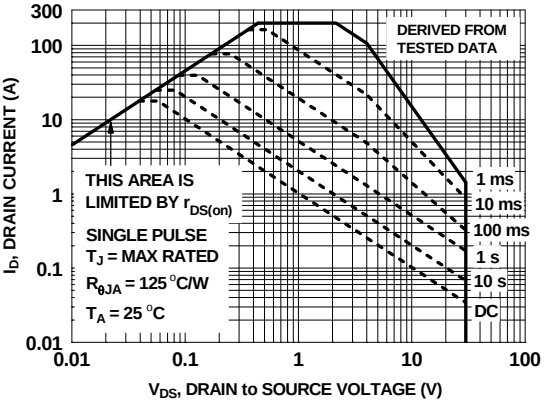


Figure 11. Forward Bias Safe Operating Area

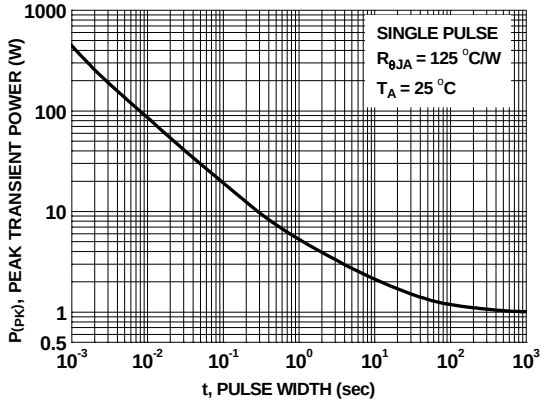


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25°C unless otherwise noted

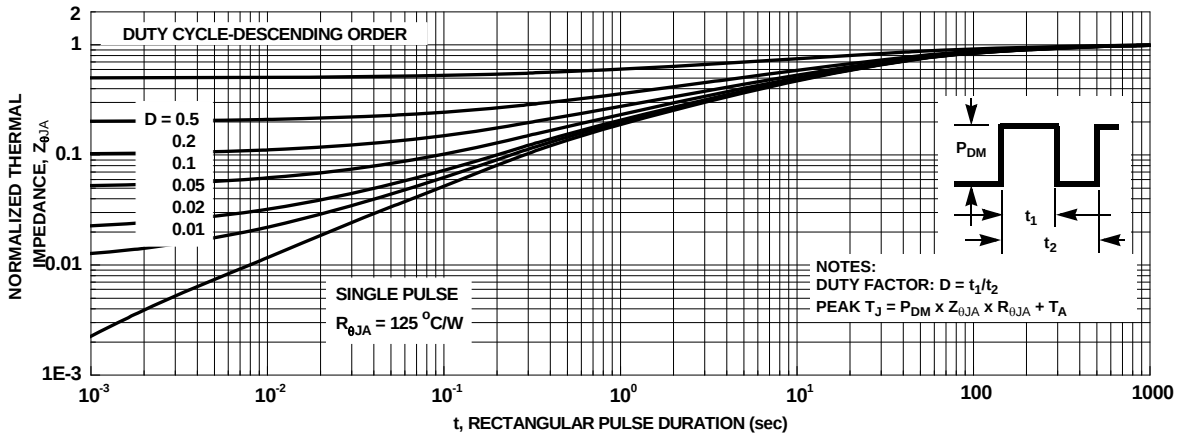
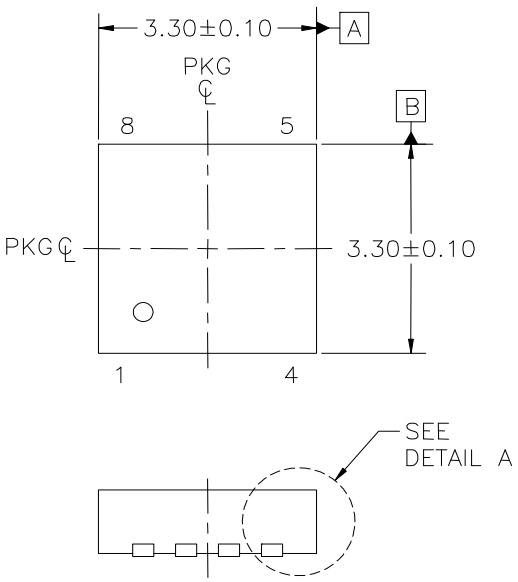
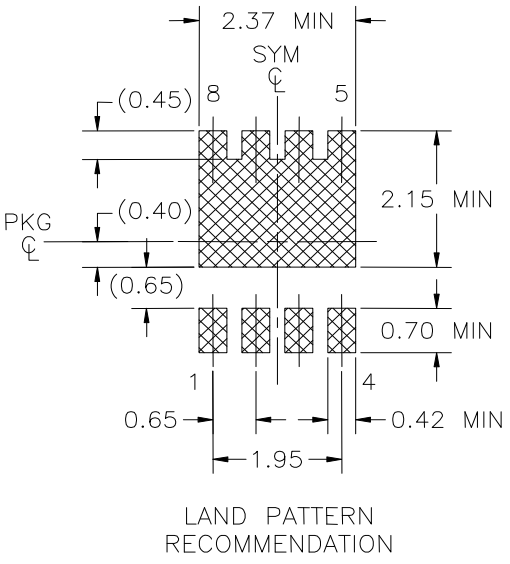


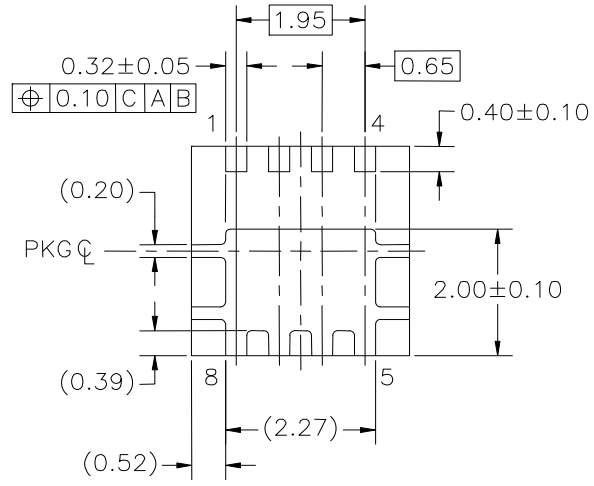
Figure 13. Junction-to-Ambient Transient Thermal Response Curve

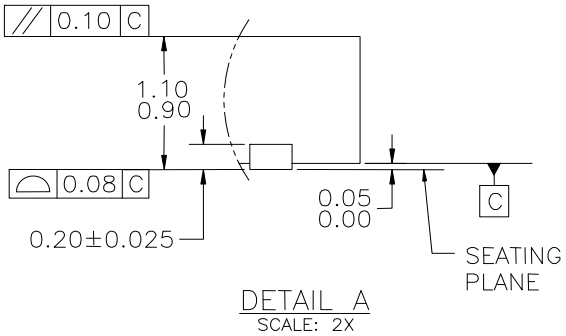
Dimensional Outline and Pad Layout





LAND PATTERN
RECOMMENDATION





DETAIL A
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

A) PACKAGE STANDARD REFERENCE: JEDEC MO−240, ISSUE A, VAR. BA, DATED OCTOBER 2002.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
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